

TSM4946D 60V Dual N-Channel MOSFET



SOP-8

Pin Definition:

1. Source 1 8. Drain 1 2. Gate 1 7. Drain 1 3. Source 2 6. Drain 2 4. Gate 2 5. Drain 2

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)		
60	55 @ V _{GS} = 10V	4.5		
	75 @ V _{GS} = 4.5V	3.9		

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Application

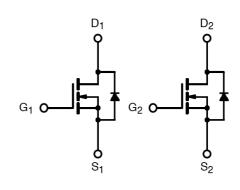
- High-Side DC/DC Conversion
- Notebook
- Sever

Ordering Information

Part No.	Package	Packing
TSM4946DCS RL	SOP-8	2.5Kpcs / 13" Reel
TSM4946DCS RLG	SOP-8	2.5Kpcs / 13" Reel

Note: "G" denote for Green Product

Block Diagram



Dual N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current		I _D	4.5	Α
Pulsed Drain Current		I _{DM}	30	Α
Continuous Source Current (Diode C	Conduction) ^{a,b}	I _S	2	Α
Mariana Baran Birahadia	Ta = 25°C	Б	2.4	\\\
Maximum Power Dissipation	Ta = 75°C	P_{D}	1.7	W
Operating Junction Temperature		T _J	+150	°C
Operating Junction and Storage Temperature Range		T _J , T _{STG}	- 55 to +150	°C

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	$R\Theta_{JF}$	32	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	$R\Theta_{JA}$	62.5	°C/W

Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, t ≤ 10 sec.

1/6 Version: B09



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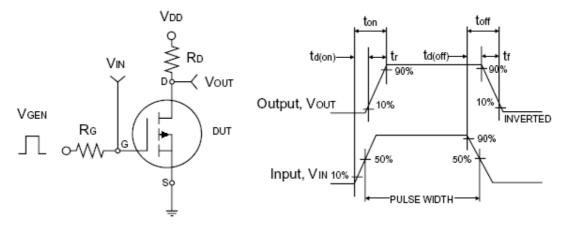


Electrical Specifications

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	60			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	1		3	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 60V, V_{GS} = 0V$	I _{DSS}			2	μΑ
On-State Drain Current ^a	$V_{DS} = 5V, V_{GS} = 10V$	I _{D(ON)}	20			Α
Dunin Course On Chata Basistanas	$V_{GS} = 10V, I_D = 4.5A$	Б		45	55	mΩ
Drain-Source On-State Resistance ^a	$V_{GS} = 4.5V, I_D = 3.9A$	R _{DS(ON)}		55	75	
Forward Transconductance ^a	$V_{DS} = 15V, I_{D} = 4.5A$	g _{fs}		13		S
Diode Forward Voltage	$I_S = 2A$, $V_{GS} = 0V$	V_{SD}		0.9	1.2	V
Dynamic ^b						
Total Gate Charge	001/1 454	Q_g		19	30	
Gate-Source Charge	$V_{DS} = 30V, I_{D} = 4.5A,$	Q_gs		4		nC
Gate-Drain Charge	V _{GS} = 10V	Q_{gd}		3		
Input Capacitance	$V_{DS} = 24V, V_{GS} = 0V,$	C _{iss}		910		
Output Capacitance		C _{oss}		145		pF
Reverse Transfer Capacitance	f = 1.0MHz	C _{rss}		67		
Switching ^c						
Turn-On Delay Time	N	t _{d(on)}		13	20	
Turn-On Rise Time	$V_{DD} = 30V, R_L = 30\Omega,$ $I_D = 1A, V_{GEN} = 10V,$	t _r		11	20	0
Turn-Off Delay Time		t _{d(off)}		36	60	nS
Turn-Off Fall Time	$R_G = 6\Omega$	t _f		11	20	

Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
- b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

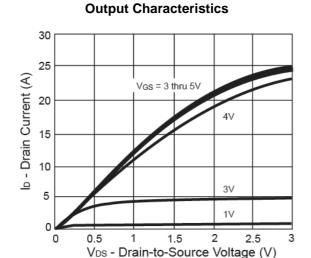
2/6 Version: B09



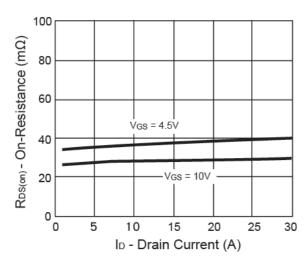
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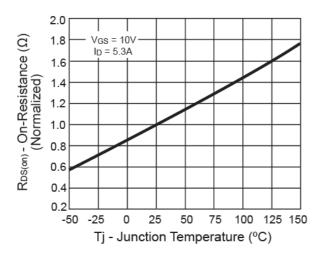
Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)



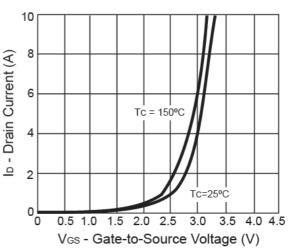
On-Resistance vs. Drain Current



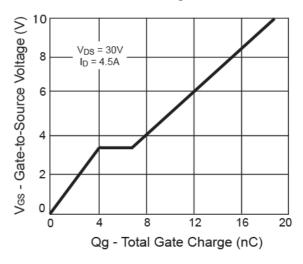
On-Resistance vs. Junction Temperature



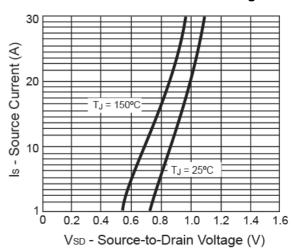
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



Version: B09

3/6

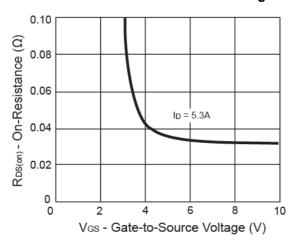


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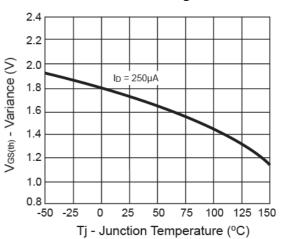


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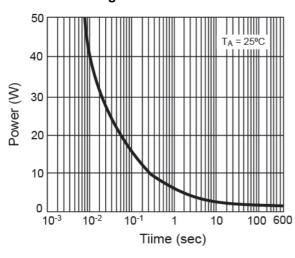
On-Resistance vs. Gate-Source Voltage



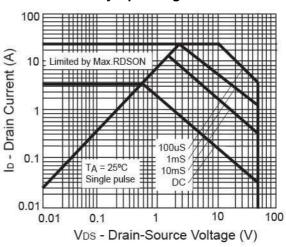
Threshold Voltage



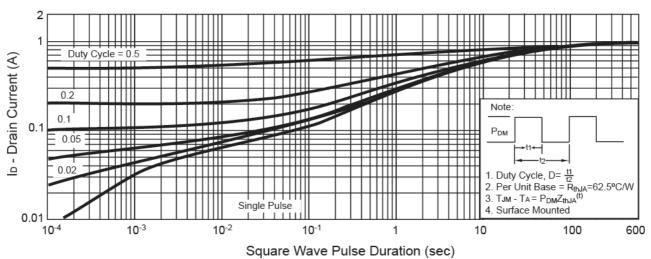
Single Pulse Power



Safety Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



4/6

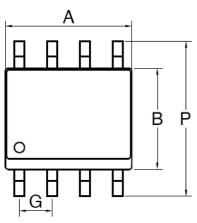
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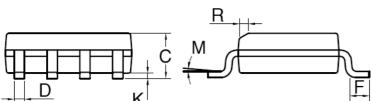


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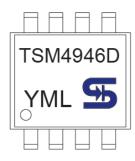
SOP-8 Mechanical Drawing





SOP-8 DIMENSION					
DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX.	
Α	4.80	5.00	0.189	0.196	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.05	BSC	
K	0.10	0.25	0.004	0.009	
М	0°	7º	00	7º	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

Marking Diagram



Y = Year Code

M = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug, I=Sep, J=Oct, K=Nov, L=Dec)

= Month Code for Halogen Free Product

5/6

(O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)

L = Lot Code

Version: B09



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6/6 Version: B09